



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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## Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of automotive applications.

## Features

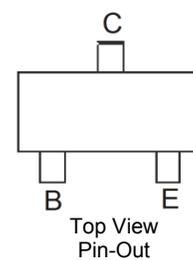
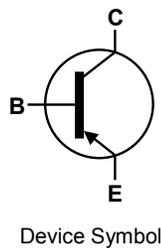
- $BV_{CEO} > -40V$
- $BV_{ECO} > -3V$
- Maximum Continuous Collector Current  $I_C = -3A$
- $R_{CE(sat)} = 55m\Omega$
- $V_{CE(sat)} < -85mV @ -1A$
- High Power Dissipation SOT23 Package
- High Peak Current
- Low Saturation Voltage
- -3V Reverse Blocking Voltage

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 2086 @3
- Weight: 0.008 grams (Approximate)

## Applications

- MOSFET and IGBT Gate Driving
- DC - DC Converters
- Motor Drives
- High-Side Drivers



**Absolute Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

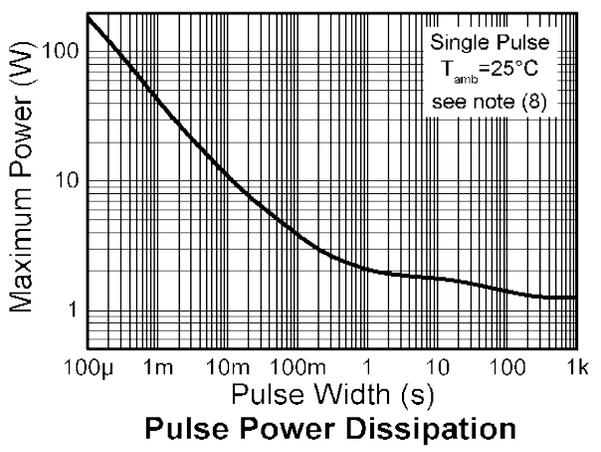
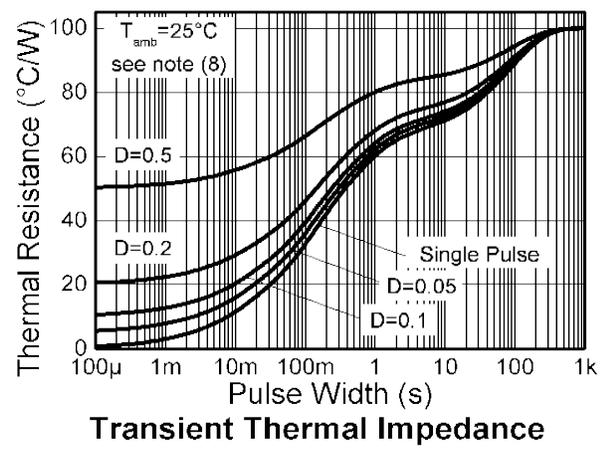
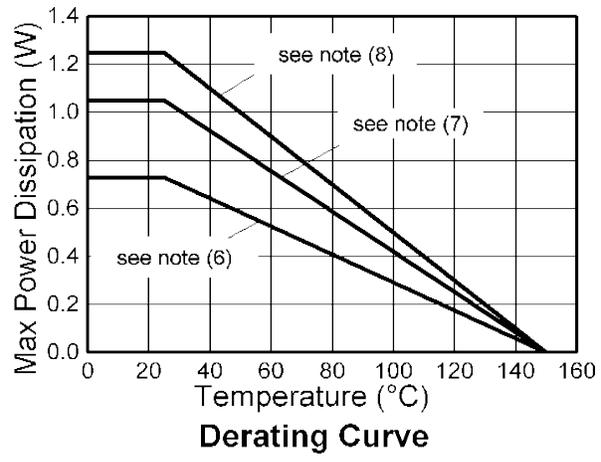
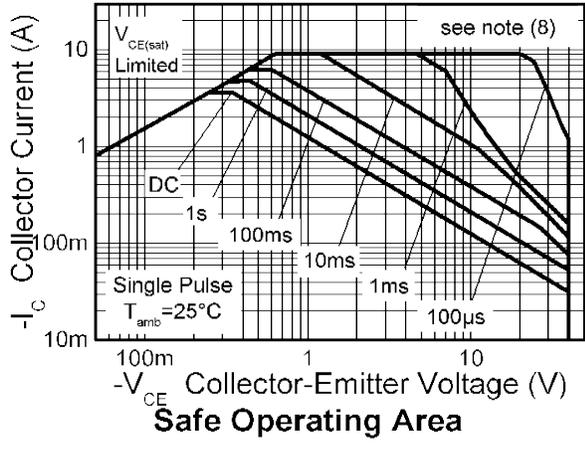
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-45	V
Collector-Emitter Voltage	$V_{CEO}$	-40	V
Emitter-Collector Voltage	$V_{ECO}$	-3	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	$I_C$	-3	A
Peak Pulse Current	$I_{CM}$	-9	A

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	$P_D$	0.73	W mW/ $^\circ\text{C}$
		5.84	
		1.05	
		8.4	
		1.25	
		9.6	
		1.81	
		14.5	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	171	$^\circ\text{C/W}$
		119	
		100	
		69	
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
5. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.
  6. Mounted on 25mm × 25mm 1.6mm FR-4 PCB with a high coverage of single sided 2oz copper in still air conditions.
  7. Mounted on 50mm × 50mm 1.6mm FR-4 PCB with a high coverage of single sided 2oz copper in still air conditions.
  8. Same as note (7), except measured at  $t < 5$  seconds.

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

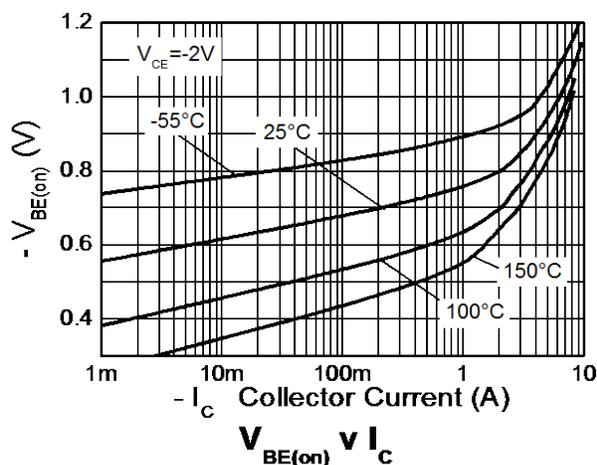
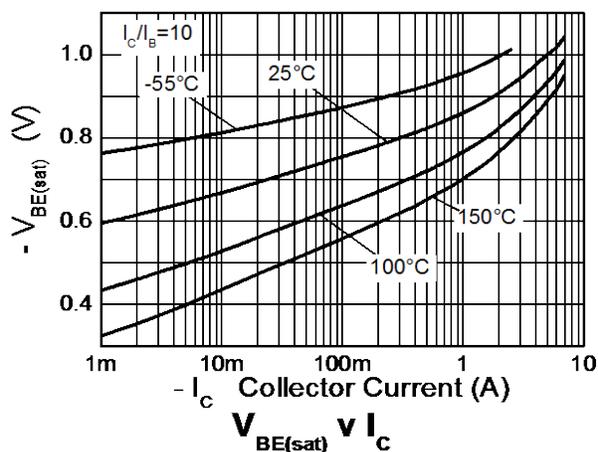
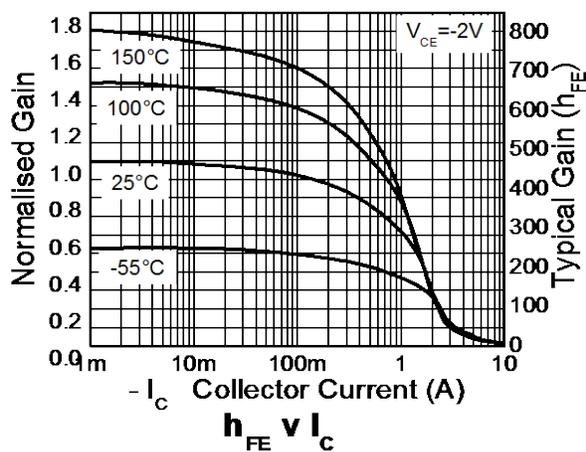
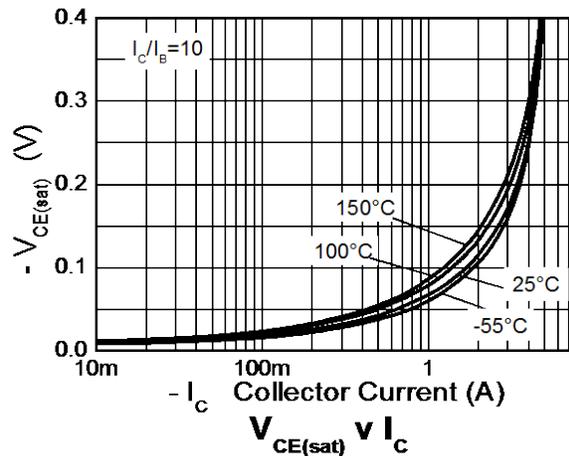
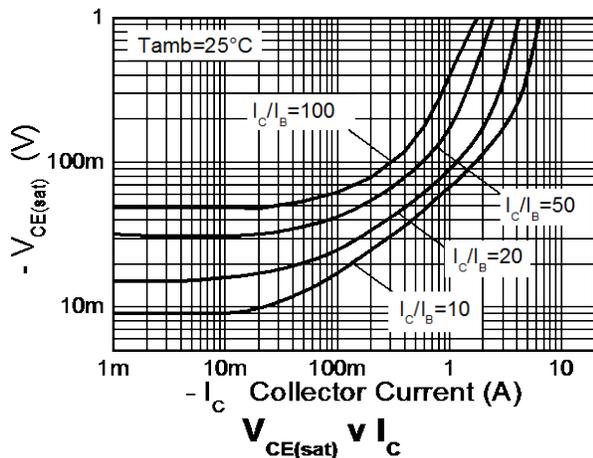


**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

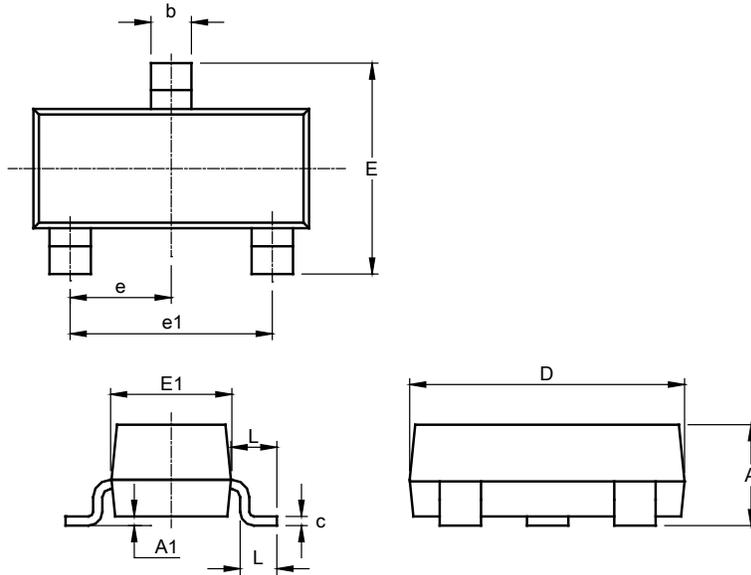
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-45	-75	—	V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 9)	$BV_{CEO}$	-40	-65	—	V	$I_C = -10\text{mA}$
Collector-Emitter Breakdown Voltage	$BV_{ECO}$	-3	-8.7	—	V	$I_E = -100\mu\text{A}$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8.2	—	V	$I_E = -100\mu\text{A}$
Collector-Base Cutoff Current	$I_{CBO}$	—	< -1	-50	nA	$V_{CB} = -45\text{V}$
		—	—	-0.5	$\mu\text{A}$	$V_{CB} = -45\text{V}, T_{amb} = 100^\circ\text{C}$
Emitter-Base Cutoff Current	$I_{EBO}$	—	< -1	-50	nA	$V_{EB} = -5.6\text{V}$
Static Forward Current Transfer Ratio (Note 9)	$h_{FE}$	300	450	900	—	$I_C = -10\text{mA}, V_{CE} = -2\text{V}$
		200	300	—		$I_C = -1\text{A}, V_{CE} = -2\text{V}$
		30	60	—		$I_C = -3\text{A}, V_{CE} = -2\text{V}$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	—	-170	-260	mV	$I_C = -1\text{A}, I_B = -20\text{mA}$
		—	-65	-85		$I_C = -1\text{A}, I_B = -100\text{mA}$
		—	-165	-220		$I_C = -3\text{A}, I_B = -300\text{mA}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	—	-930	-1000	mV	$I_C = -3\text{A}, I_B = -300\text{mA}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(on)}$	—	-830	-900	mV	$I_C = -3\text{A}, V_{CE} = -2\text{V}$
Output Capacitance (Note 9)	$C_{obo}$	—	17.4	—	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Transition Frequency	$f_T$	—	270	—	MHz	$V_{CE} = -10\text{V}, I_C = -50\text{mA}, f = 100\text{MHz}$
Turn-On Time	$t_{on}$	—	75.5	—	ns	$V_{CC} = -15\text{V}, I_C = -750\text{mA}, I_{B1} = -I_{B2} = -15\text{mA}$
Turn-Off Time	$t_{off}$	—	320	—		

 Note: 9. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

**Typical Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

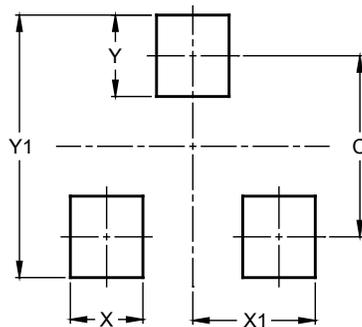


**Package Outline Dimensions**



SOT23 (Type DN)			
Dim	Min	Max	Typ
A	0.89	1.12	1.00
A1	0.01	0.10	0.05
b	0.30	0.51	0.45
c	0.08	0.20	0.10
D	2.80	3.04	3.00
E	2.10	2.64	2.42
E1	1.20	1.40	1.37
e	0.95 REF		
e1	1.90 REF		
L	0.25	0.60	0.30
L1	0.45	0.62	0.54
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9